

The Rules of IEEE Format on Reference LIST

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I. Journal article format

「 Author(s), “Title of article,” *Name of Journal*, volume number, issue number, page range, month year. 」

Examples:

- [1] H.-W. Tsai and M.-D. Ker, “Active guard ring to improve latchup immunity,” *IEEE Trans. Electron Devices*, vol. 61, no. 12, pp. 4145–4152, Dec. 2014.
- [2] W.-J. Chang and M.-D. Ker, “The impact of drift implant and layout parameters on ESD robustness for on-chip ESD protection devices in 40-V CMOS technology,” *IEEE Trans. Device Mater. Rel.*, vol. 7, no. 2, pp. 324–332, Jun. 2007.
- [3] M.-D. Ker, H.-H. Chang, and C.-Y. Wu, “A gate-coupled PTLSCR/NTLSCR ESD protection circuit for deep-submicron low-voltage CMOS IC’s,” *IEEE J. Solid-State Circuits*, vol. 32, no. 1, pp. 38–51, Jan. 1997.
- [4] C.-Y. Lin, W.-L. Chen, and M.-D. Ker. “Implantable stimulator for epileptic seizure suppression with loading impedance adaptability,” *IEEE Trans. on Biomedical Circuits and Systems*, vol. 7, no. 2, pp. 196–203, Apr. 2013.
- [5] R. Sun, Z. Wang, M. Klebanov, W. Liang, J. Liou, and D. Liu, “Silicon-controlled rectifier for electrostatic discharge protection solutions with minimal snapback and reduced overshoot voltage,” *IEEE Electron Device Letters*, vol. 36, no. 5, pp. 424-426, May 2015.

Remarks:

- a.) Pay attention to the spacing between words and the comma placements.
- b.) The authors’ names should be abbreviated.
- c.) The comma placement for authors is dependent on the number of authors. For two authors, comma is not used. (e.g., A and B.) For three or more authors, each author’s name is followed by a comma. ‘And’ is used before the final author. (e.g., A, B, C, and D.)
- d.) Title of the article is in quotation marks and followed by a comma. Use upper case for the first letter of the title and lower case for the rest unless referring to proper nouns.
- e.) Name of the journal is in italics. Use capital letters at the start of all key words. Spell out the entire name of each journal or use its accepted abbreviations. It must be consistently done for all referenced paper.
- f.) The format of journal article ends with month and year of the publication.

II. Conference article format

「 Author(s), “Title of article,” *Name of Conference*, year, page range. 」

Examples:

- [1] S.-H. Chen, D. Linten, G. Hellings, A. Veloso, M. Scholz, R. Boschke1, G. Groeseneken, N. Collaert, and A. Thean, “ESD characterization of gate-all-around (GAA) Si nanowire devices,” in *IEDM Tech. Dig.*, 2015, pp. 14.4.1–14.4.4.
- [2] C. Fu, H. Lakdawala, S. Taylor, and K. Soumyanath, “A 2.5GHz 32nm 0.35mm² 3.5dB NF -5dBm P_{1dB} fully differential CMOS push-pull LNA with integrated 34dBm T/R switch and ESD protection,” in *ISSCC Dig. Tech. Papers*, 2011, pp. 56–57.
- [3] C. Chiang, P.-C. Chang, P.-S. Tseng, P.-Y. Lai, T.-H. Tang, and K.-C. Su, “Optimization of PESD implant design for ESD robustness of 5V drain-back N-LDMOSFET,” in *Proc. IEEE Int. Reliability Physics Symp.*, 2016, pp. EL-3-1–EL-3-4.
- [4] J.-W. Lee, Y.-F. Chang, C.-W. Hsu, T.-C. Tsai, W.-Y. Lin, and M.-H. Song, “Novel isolation ring structure for latch-up and power efficiency improvement of smart power IC’s,” in *Proc. EOS/ESD Symp.*, 2013, pp. 1–5.
- [5] Y. Lu, J. Jiang, W.-H. Ki, C. P. Yue, S.-W. Sin, S.-P. U, and R. P. Martins, “A 123-phase DC-DC converter-ring with fast-DVS for microprocessors,” in *IEEE Int. Solid-State Circuits Conf. Dig. Tech. Papers*, 2015, pp. 363–365.

Remarks:

- a.) The conference papers are recorded in the conference proceedings, and generally written as “in *Proc. of conference name.*”
- b.) The paper recorded in International Electron Devices Meeting (IEDM) is written as “in *IEDM Tech. Dig.*”, and in International Solid-State Circuits Conference (ISSCC) is “in *ISSCC Dig. Tech. Papers*”.
- c.) The format of conference article is a little different with the journal article. It doesn’t have volume and issue numbers, and ends with page range.

III. Book format

「 Author(s), *Title of Book*. City, state, and nation of publication: Publisher, Year of publication. 」

Examples:

- [1] M.-D. Ker and S.-F. Hsu, *Transient-Induced Latchup in CMOS Integrated Circuits*. New York, NY, USA: Wiley, 2009.
- [2] V. A. Vashchenko and A. Shibkov, *ESD Design for Analog Circuits*. New York, NY, USA: Springer, 2010.

[3] S. H. Voldman, *Latchup*. Hoboken, NJ, USA: Wiley, 2007.

Remarks:

- a.) Title of the book is in italics and followed by a full stop. Use upper case for the first letter of the title and all key words.
- b.) City of publication is followed by a colon. Publisher is followed by a comma and year of publication.

IV. Standard format

「 *Title of Standard*, Standard number, Year. 」

Examples:

- [1] *IC Latch-Up Test*, JEDEC Solid State Technology Association, JEDEC Standard JESD78D, 2011.
- [2] *Electrostatic Discharge (ESD) Sensitivity Testing: Human Body Model (HBM)—Component Level*, ESD Association Standard ANSI/ESDA/JEDEC JS-001-2014, 2014.
- [3] *EMC-Part 4-4: Testing and Measurement Techniques-Electrical Fast Transient/Burst Immunity Test*, International Standard IEC 61000-4-4, 2004.

V. Patent format

「 Author(s), “Title of patent,” Patent number, Date, Year. 」

Examples:

- [1] F. A. Altolaguirre, M.-D. Ker, and H.-C. Jiang, “Power-rail electrostatic discharge (ESD) clamp circuit,” U.S. Patent 8773826 B2, Jul. 27, 2014.

VI. Additional Remarks

- For anything is not clear, please go to find the already published papers in the IEEE Transactions (or Journal) to seek the Rules/Formats for writing down the Reference List in your documents/manuscripts.
- The Reference List in the published papers in IEEE Conferences / Symposiums / Workshops may not follow the *Rules/Formats* those used in IEEE Transactions (or Journal). Do NOT use the Conference Format to write your manuscripts for Transactions (or Journal) papers and your Thesis.